

wherein a plurality of said pixel electrodes are formed in a pixel portion and an insulator is formed in each space between said pixel electrodes, and

wherein a thickness of a portion of the insulator higher than a top surface of the pixel electrodes is 0.1 to 1 μ m.

22. (Currently Amended) A self-light-emitting device comprising:

at least first and second switching elements;

at least one interlayer insulating film formed over said first and second switching elements;

at least first and second pixel electrodes formed over said interlayer insulating film wherein said first and second pixel electrodes are electrically connected to said first and second switching elements, respectively;

an insulating layer formed in a gap between said first and second pixel electrodes;

a light emitting layer formed over said first and second pixel electrodes and said insulating layer; and

a third electrode formed over said light emitting layer opposed to said first and second pixel electrodes,

wherein a thickness of a portion of the insulating layer higher than a top surface of the pixel electrodes is 0.1 to 1 μ m.